

IN THE CLAIMS

Please amend the following claims. Please cancel claims 6, and 15-29.

Please add new claim 30.

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1. (Currently Amended) An apparatus comprising:
 - a plasma chamber containing a plasma for a plasma-assisted material process upon a substrate;
 - a solid shielding plate within said plasma chamber disposed between the substrate and a gas inlet of the plasma chamber to actively direct ion flux to desired areas of the substrate; and
 - a supporting structure to support said shielding plate within said chamber.
2. (Original) The apparatus of claim 1 wherein the plasma-assisted material process is a plasma-assisted etching process.
3. (Original) The apparatus of claim 1 wherein the plasma-assisted material process is a plasma-enhanced chemical vapor deposition process.
4. (Original) The apparatus of claim 1 wherein the solid shielding plate and the supporting structure are composed of a dielectric material.
5. (Original) The apparatus of claim 1 wherein the supporting structure further comprises three or more supporting members.

6. (Cancelled).

7. (Currently Amended) The apparatus of claim 1 wherein the solid shielding plate is shaped to concentrate etching within a desired area of the substrate has one or more perforations that allow ion flux to pass, such that the ion flux within a localized area of the substrate is fitted to meet the requirements of a desired material process.

8. (Currently Amended) The apparatus of claim 1 wherein the dimensions of the solid shielding plate are dependent upon the dimensions of the plasma chamber and the substrate.

9. (Currently Amended) The apparatus of claim 8 wherein the thickness of the solid shielding plate is 2-5 mm.
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10. (Original) The apparatus of claim 1 wherein the distance between a member of said supporting structure and said substrate is greater than the mean free path of a reactive particle.

11. (Currently Amended) The apparatus of claim 1 wherein the width of a member of said supporting plate structure is less than the mean free path of a reactive particle.

12. (Currently Amended) The apparatus of claim 1 wherein the edge of said solid shielding plate is rounded.

13. (Currently Amended) The apparatus of claim 1 wherein the solid shielding plate is circular.

14. (Original) The apparatus of claim 1 wherein the plasma-assisted material process is carried out in high-density plasma.

15 –29 (Cancelled).

30. (New) An apparatus comprising:

a plasma chamber; containing a plasma for a plasma-assisted material process upon a substrate;

a gas inlet to introduce reactive gas into the plasma chamber;

a pedestal to set a substrate while conducting a plasma-assisted material process upon the substrate; and

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a shield disposed between the gas inlet and the pedestal, the shield directing an ion flux within the plasma chamber to alter the plasma-assisted material process.